

## Super FAP-G Series

## N-CHANNEL SILICON POWER MOSFET

### ■ Features

- High speed switching
- No secondary breakdown
- Avalanche-proof
- Low on-resistance
- Low driving power

### ■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

### ■ Maximum ratings and characteristic Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V <sub>DS</sub>	450	V	
	V <sub>DSX</sub>	450	V	V <sub>GS</sub> =-30V
Continuous drain current	I <sub>D</sub>	6	A	
Pulsed drain current	I <sub>D(puls)</sub>	±24	A	
Gate-source voltage	V <sub>GS</sub>	±30	V	
Repetitive or non-repetitive	I <sub>AR</sub>	6	A	Note *1
Non-repetitive Maximum avalanche energy	E <sub>AS</sub>	320	mJ	Note *2
Repetitive Maximum avalanche energy		3.2	mJ	Note *3
Maximum drain-source dV/dt	dV <sub>DS</sub> /dt	20	kV/μs	V <sub>DS</sub> ≤ 450V
Peak diode recovery dV/dt	dV/dt	5	kV/μs	Note *4
Maximum power dissipation	P <sub>D</sub>	2.16	W	T <sub>a</sub> =25°C
		32	W	T <sub>c</sub> =25°C
Operating and storage temperature range	T <sub>ch</sub> T <sub>stg</sub>	+150 -55 to +150	°C	
Isolation voltage	V <sub>ISO</sub> *6	2	kVrms	t=60sec, f=60Hz

Note \*1 T<sub>ch</sub> ≤ 150°C

Note \*2 Starting T<sub>ch</sub>=25°C, I<sub>AS</sub>=6A, L=102mH, V<sub>CC</sub>=45V, R<sub>G</sub>=50Ω

E<sub>AS</sub> limited by maximum channel temperature and avalanche current.  
See to 'Avalanche Energy' graph.

Note \*3 Repetitive rating : Pulse width limited by maximum channel temperature.  
See to 'Transient Thermal impedance' graph.

Note \*4 I<sub>SR</sub> ≤ -I<sub>D</sub>, -di/dt=50A/μs, V<sub>CC</sub> ≤ BV<sub>DSS</sub>, T<sub>ch</sub> ≤ 150°C

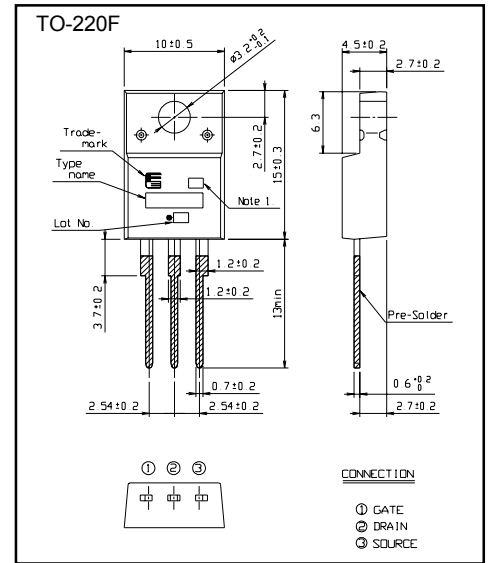
### ● Electrical characteristics (T<sub>c</sub> =25°C unless otherwise specified)

Item	Symbol	Test Conditions				
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250μA V <sub>GS</sub> =0V	450			V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> = 250μA V <sub>DS</sub> =V <sub>GS</sub>	3.0		5.0	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =450V V <sub>GS</sub> =0V			25	μA
		V <sub>DS</sub> =360V V <sub>GS</sub> =0V			2.0	mA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V			100	nA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =3A V <sub>GS</sub> =10V		0.98	1.20	Ω
Forward transconductance	g <sub>fs</sub>	I <sub>D</sub> =3A V <sub>DS</sub> =25V	2.5	5		S
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		440	660	pF
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		67	100	
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz		2.8	4.5	ns
Turn-on time t <sub>on</sub>	td(on)	V <sub>CC</sub> =300V I <sub>D</sub> =3A		12	18	
	t <sub>r</sub>	V <sub>GS</sub> =10V		6.5	10	
Turn-off time t <sub>off</sub>	td(off)	R <sub>GS</sub> =10 Ω		25	38	
	t <sub>r</sub>			5.5	8.5	
Total Gate Charge	Q <sub>G</sub>	V <sub>CC</sub> =225V		15.5	23.5	nC
Gate-Source Charge	Q <sub>GS</sub>	I <sub>D</sub> =6A		6.8	10.5	
Gate-Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> =10V		3.7	5.5	
Diode forward on-voltage	V <sub>SD</sub>	I <sub>F</sub> =6A V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1.00	1.50	V
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =6A V <sub>GS</sub> =0V		300		ns
Reverse recovery charge	Q <sub>rr</sub>	-di/dt=100A/μs T <sub>ch</sub> =25°C		2.0		μC

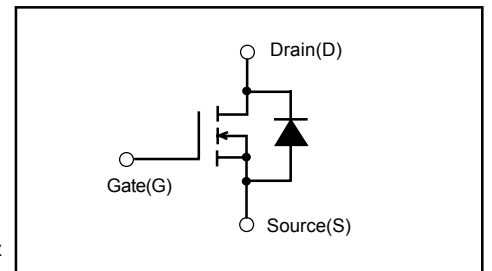
### ● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R <sub>th(ch-c)</sub>	channel to case			3.906	°C/W
	R <sub>th(ch-a)</sub>	channel to ambient			58.0	°C/W

### ■ Outline Drawings [mm]



### ■ Equivalent circuit schematic



Characteristics

